



## PJQ5544-AU

### 40V N-Channel Enhancement Mode MOSFET

**Voltage**    **40 V**    **Current**    **130 A**

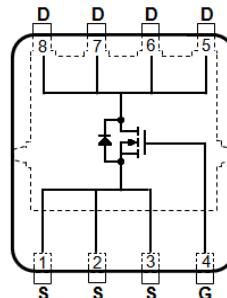
#### Features

- $R_{DS(ON)}$ ,  $V_{GS} @ 10V$ ,  $I_D @ 20A < 3.3m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS} @ 4.5V$ ,  $I_D @ 20A < 4.3m\Omega$
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### Mechanical Data

- Case : DFN5060-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.08 grams

DFN5060-8L



#### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>(Note 3)</sup>	$I_D$	130	A
		92	
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	520	A
Power Dissipation	$P_D$	100	W
		50	
Continuous Drain Current <sup>(Note 4)</sup>	$I_D$	24	A
		20	
Power Dissipation	$P_D$	3.3	W
		2.3	
Single Pulse Avalanche Energy <sup>(Note 5)</sup>	$E_{AS}$	225	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~175	°C
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	$R_{\theta JC}$	1.5
	Junction to Ambient	$R_{\theta JA}$	45



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### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	40	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=50\mu\text{A}$	1.1	1.6	2.3	
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=20\text{A}$	-	2.6	3.3	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=20\text{A}$	-	3.3	4.3	
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=40\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	$\text{nA}$
<b>Dynamic</b> <sup>(Note 6)</sup>						
Total Gate Charge	$Q_g$	$V_{\text{DS}}=32\text{V}, I_{\text{D}}=20\text{A}, V_{\text{GS}}=10\text{V}$	-	41	-	$\text{nC}$
Gate-Source Charge	$Q_{\text{gs}}$		-	7	-	
Gate-Drain Charge	$Q_{\text{gd}}$		-	5	-	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	2851	-	$\text{pF}$
Output Capacitance	$C_{\text{oss}}$		-	497	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	49	-	
Gate resistance	$R_g$	$f=1\text{MHz}$	-	1	-	$\Omega$
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DS}}=32\text{V}, I_{\text{D}}=20\text{A}, V_{\text{GS}}=10\text{V}, R_{\text{G}}=3\Omega$ <small>(Note 2)</small>	-	15	-	$\text{ns}$
Turn-On Rise Time	$t_r$		-	5	-	
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	46	-	
Turn-Off Fall Time	$t_f$		-	10	-	
<b>Drain-Source Diode</b>						
Diode Forward Current	$I_s$	$T_c=25^\circ\text{C}$	-	-	130	$\text{A}$
Pulsed Diode Forward Current	$I_{\text{SM}}$		-	-	520	
Diode Forward Voltage	$V_{\text{SD}}$	$I_s=20\text{A}, V_{\text{GS}}=0\text{V}$	-	0.8	1.3	$\text{V}$
Reverse Recovery Time	$T_{\text{rr}}$	$V_{\text{GS}}=0\text{V}, I_s=20\text{A}$ $dI_s/dt=100\text{A}/\mu\text{s}$	-	38	-	$\text{ns}$
Reverse Recovery Charge	$Q_{\text{rr}}$		-	35	-	

#### NOTES :

1. Pulse width  $\leq 100\mu\text{s}$ , Duty cycle  $\leq 2\%$ .
2. Essentially independent of operating temperature typical characteristics.
3. Chip capability with an  $R_{\theta\text{JC}}=1.5^\circ\text{C}/\text{W}$ , Pakage limited 100A.
4.  $R_{\theta\text{JA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
5. The test condition is  $L=0.5\text{mH}, I_{\text{AS}}=30\text{A}, V_{\text{DD}}=30\text{V}, V_{\text{GS}}=10\text{V}$ , Starting  $T_j=25^\circ\text{C}$ .
6. Guaranteed by design, not subject to production testing.



## PJQ5544-AU

### TYPICAL CHARACTERISTIC CURVES

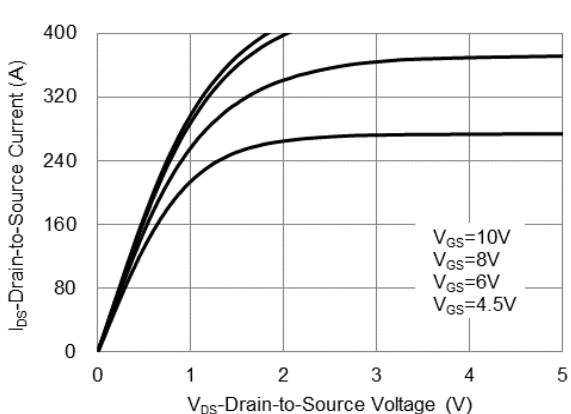


Fig.1 On-Region Characteristics

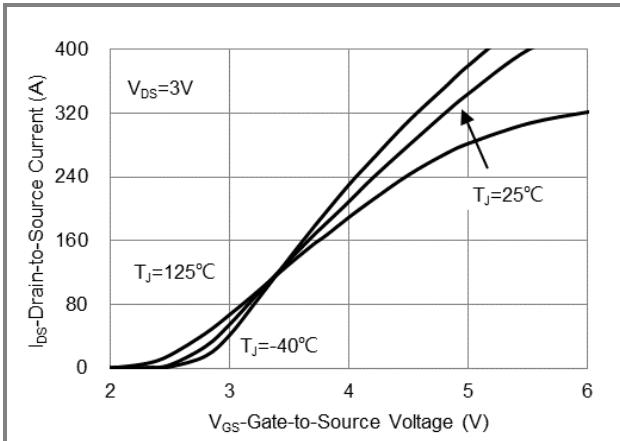


Fig.2 Transfer Characteristics

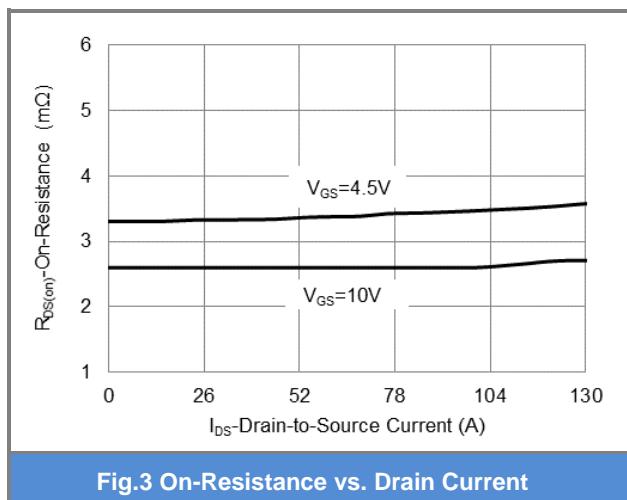


Fig.3 On-Resistance vs. Drain Current

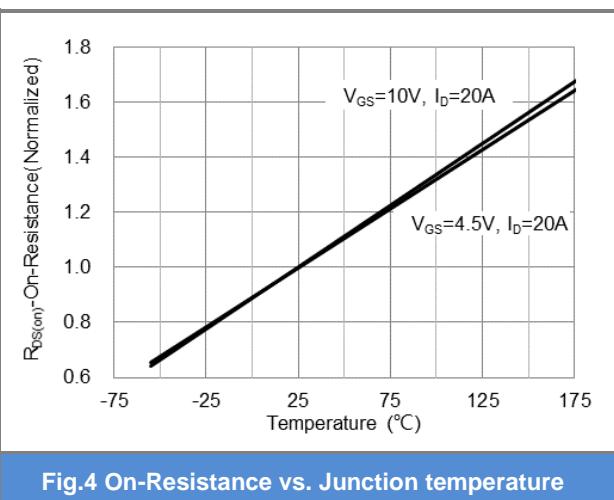


Fig.4 On-Resistance vs. Junction temperature

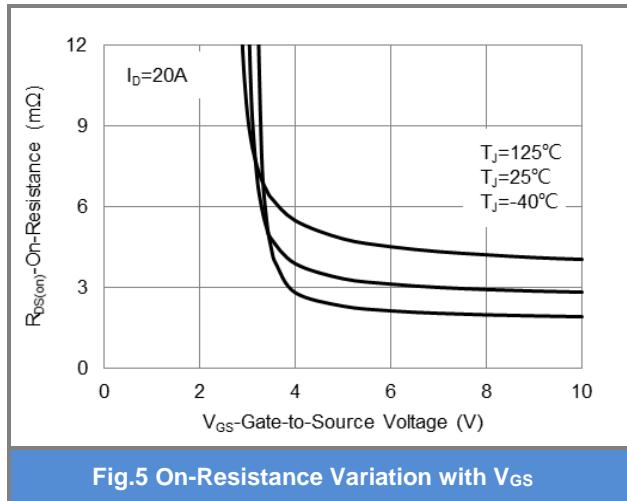


Fig.5 On-Resistance Variation with Vgs

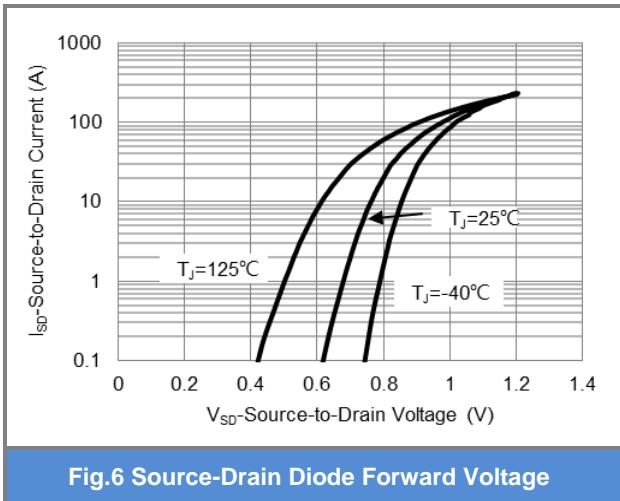


Fig.6 Source-Drain Diode Forward Voltage



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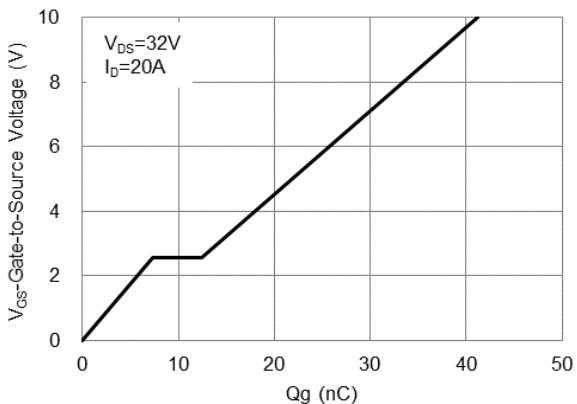


Fig.7 Gate-Charge Characteristics

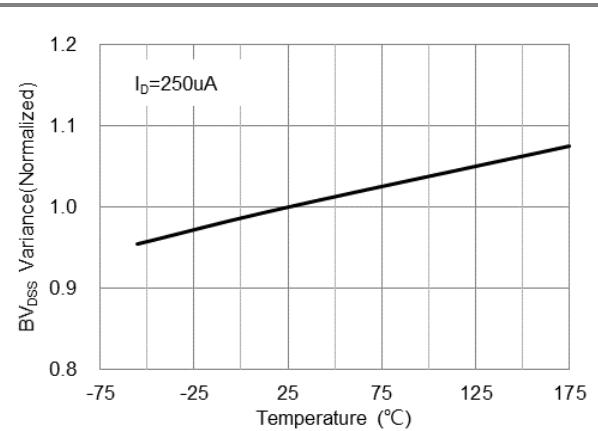


Fig.8 Breakdown Voltage Variation vs. Temperature

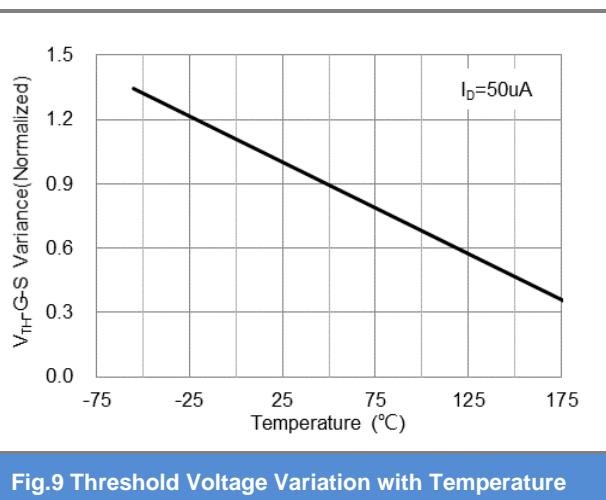


Fig.9 Threshold Voltage Variation with Temperature

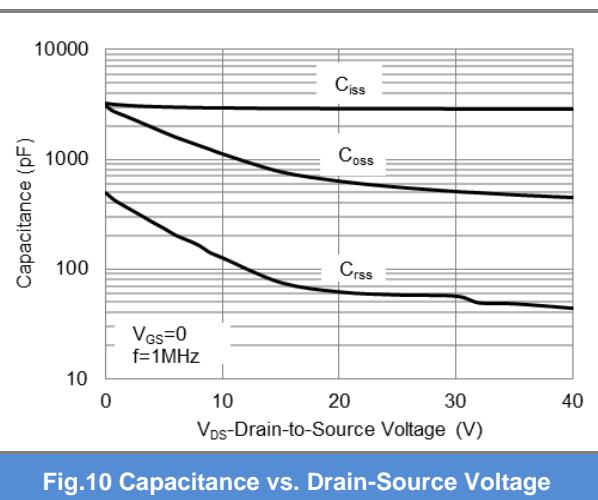


Fig.10 Capacitance vs. Drain-Source Voltage

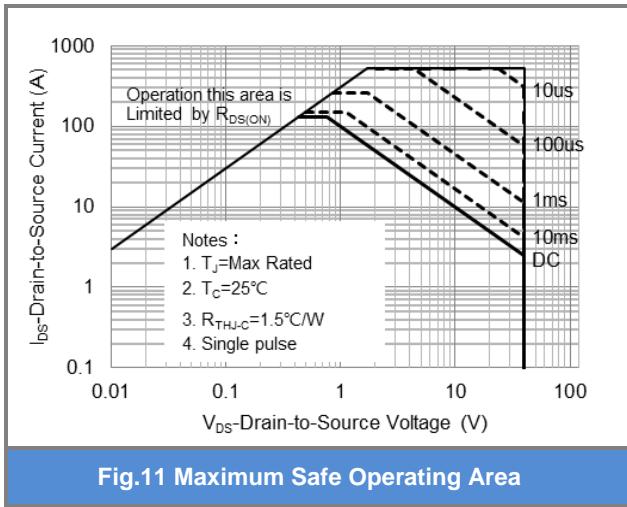


Fig.11 Maximum Safe Operating Area

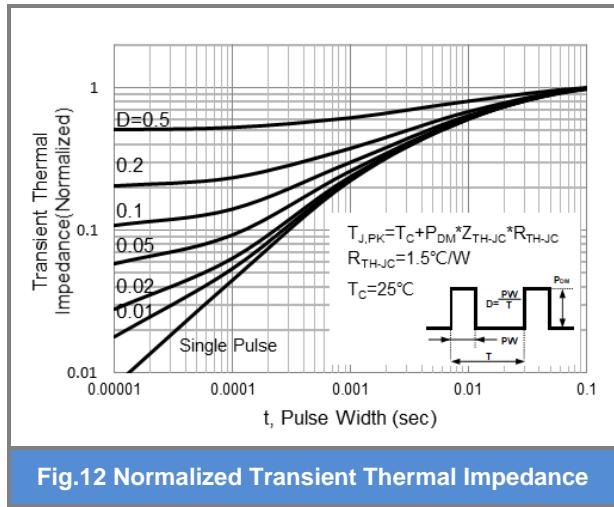


Fig.12 Normalized Transient Thermal Impedance



## PJQ5544-AU

### Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ5544-AU	DFN5060-8L	3K pcs / 13" reel	Q5544

### Packaging Information & Mounting Pad Layout

